



### 80V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

# **Product Summary**

BV <sub>DSS</sub>	Rds(ON)	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 11)
80V	$3.8$ m $\Omega$ @ V <sub>GS</sub> = $10$ V	100A
	5.3mΩ @ V <sub>GS</sub> = 4.5V	100A

### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low RDS(ON) Minimizes On-State Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

## **Description and Applications**

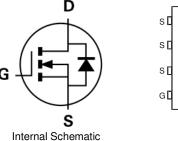
This new generation MOSFET is designed to minimize R<sub>DS(ON)</sub>, yet maintain superior switching performance. This device is ideal for use in power management and load switch.

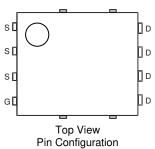
- DC-DC Converters
- Load Switch

### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 3
- Weight: 0.097 grams (Approximate)







### **Ordering Information** (Note 4)

Part Number	Case	Packaging	
DMTH8004LPS-13	PowerDI5060-8	2,500/Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



);; = Manufacturer's Marking
TH8004LPS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 19 = 2019)
WW = Week (01 to 53)



## **Maximum Ratings** (@ $T_C = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	80	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 7)	lp	100 100	А		
Maximum Continuous Body Diode Forward Current (No	ls	83	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	400	Α		
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			Ism	400	Α
Avalanche Current, L = 0.3mH (Note 8)			las	35	A
Avalanche Energy, L = 0.3mH (Note 8)			Eas	183.7	mJ

# Thermal Characteristics (@Tc = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	101	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	51	°C/W
Total Power Dissipation (Note 7)	$T_C = +25^{\circ}C$	P <sub>D</sub>	125	W
Thermal Resistance, Junction to Case (Note 7)		Rejc	1.2	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +175	°C

## **Electrical Characteristics** (@Tc = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80			V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS		_	1	μΑ	$V_{DS} = 64V$ , $V_{GS} = 0V$	
Gate-Source Leakage	Igss	_		±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	$V_{GS(TH)}$	1.3		2.8	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Chatia Duain Causas On Desistanas		_	2.8	3.8	0	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	
Static Drain-Source On-Resistance	RDS(ON)	_	3.9	5.3	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A	
Diode Forward Voltage	$V_{SD}$	_	0.8	1.2	V	$V_{GS} = 0V, I_S = 20A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		4979	_		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	1166	_	pF		
Reverse Transfer Capacitance	Crss		71	_			
Gate Resistance	Rg	_	2.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (VGS = 4.5V)	Qg	_	43	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	_	81	_	nC	V <sub>DD</sub> = 40V, I <sub>D</sub> = 20A	
Gate-Source Charge	Qgs	_	14	_	nC		
Gate-Drain Charge	QgD	_	22	_			
Turn-On Delay Time	tD(ON)	_	8.5	_			
Turn-On Rise Time	tr	_	11.8	_		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 20A, R_{G} = 1.6\Omega$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	55	_	ns		
Turn-Off Fall Time	tF	_	27.7	_			
Body Diode Reverse Recovery Time	trr	_	53	_	ns	I_ 000 di/dt 1000/us	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	91	_	nC	IF = 20A, di/dt = 100A/μs	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25$ °C.
- S. Jas and Lag ratings are based on how frequency and duty cycle
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.
   Package limited.



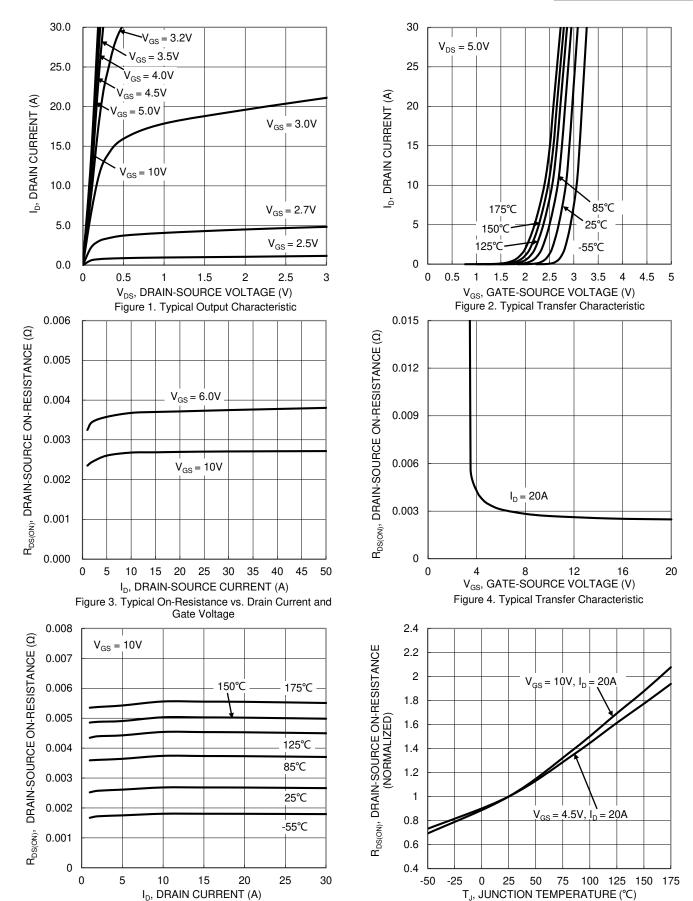
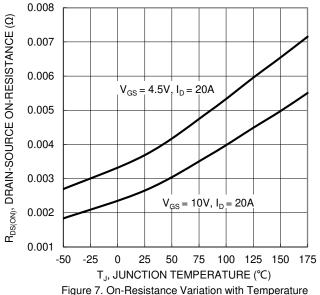


Figure 5. Typical On-Resistance vs. Drain Current and

Temperature

Figure 6. On-Resistance Variation with Temperature





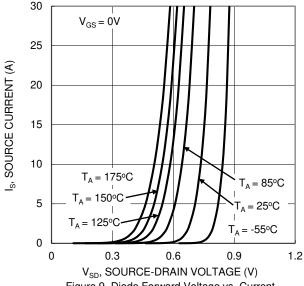
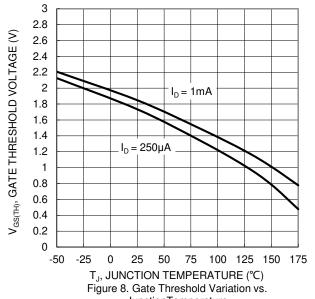
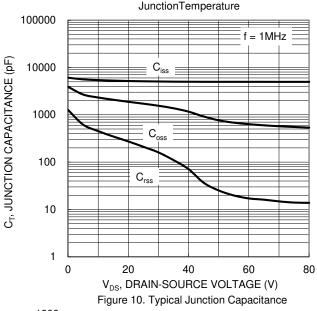
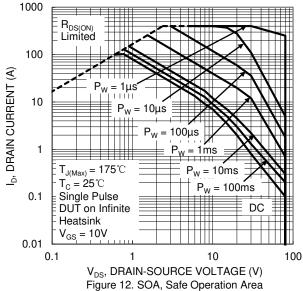


Figure 9. Diode Forward Voltage vs. Current 10 8 6  $V_{GS}(V)$ 4  $V_{DS} = 40V, I_{D} = 20A$ 2 0 0 10 20 30 40 50 60 70 80  $Q_g$  (nC) Figure 11. Gate Charge









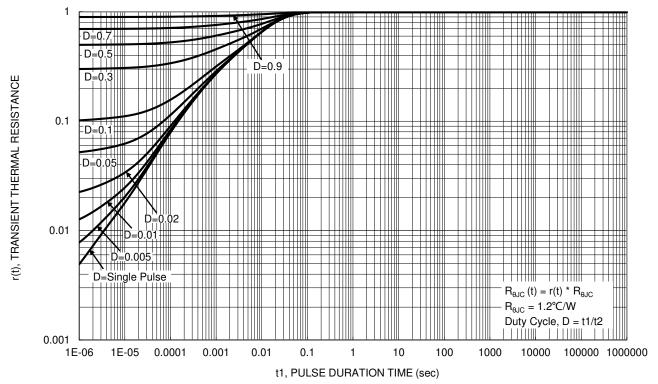


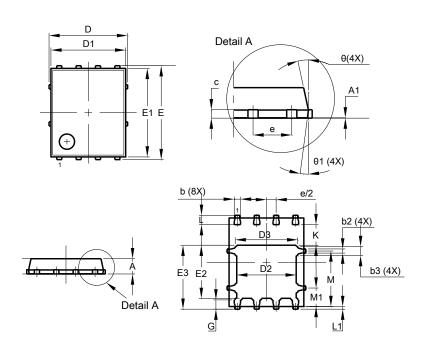
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

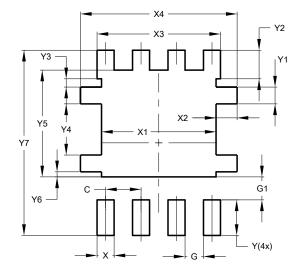


PowerDI5060-8						
Dim	Min         Max         Typ           0.90         1.10         1.00					
Α	0.90	0.90 1.10				
A1	0.00	0.05	_			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D	ţ	5.15 BSC	;			
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90					
E		6.15 BSC	;			
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99					
е		1.27 BSC				
G	0.51	0.71	0.61			
K	0.51	-	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10°	12°	11°			
Θ1	6°	8°	7°			
All	All Dimensions in mm					

# **Suggested Pad Layout**

 $Please \ see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

### PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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